

IN THE CLAIMS

1 (Currently Amended). A method comprising:
positioning a conductive surface of a semiconductor wafer on a conductive
polishing pad; and
providing electrical contact to said surface across the pad; and.
providing electrodes in contact with said surface, said electrodes extending
through said pad, said electrodes being of opposite polarity to said contact.

Claims 2-4 (Canceled).

5 (Currently Amended). The method of claim 1 –2– including providing circularly
shaped openings in said pad over said electrodes.

6 (Original). The method of claim 1 including positioning said pad over a conductive
platen.

7 (Original). The method of claim 5 including insulating said electrode from said pad.

8 (Original). The method of claim 1 including providing said pad over a conductive
platen and applying potential to said film through said pad and platen.

9 (Original). The method of claim 1 including providing electrical contact to said
surface over the entire extent of said surface.

10 (Original). The method of claim 1 including applying pressure between said surface
and said pad.

11 (Original). The method of claim 1 including providing an abrasive fluid between said
surface and said pad.

12 (Original). The method of claim 1 including counter rotating said pad and said surface.

Claims 13-19 (Canceled).